

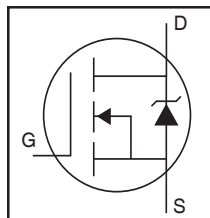
IRFR4510PbF

IRFU4510PbF

HEXFET® Power MOSFET

Applications

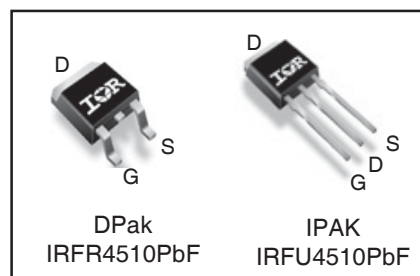
- High Efficiency Synchronous Rectification in SMPS
- Uninterruptible Power Supply
- High Speed Power Switching
- Hard Switched and High Frequency Circuits



V_{DSS}	100V
R_{DS(on)} typ.	11.1mΩ
max.	13.9mΩ
I_D (Silicon Limited)	63A
I_D (Package Limited)	56A

Benefits

- Improved Gate, Avalanche and Dynamic dV/dt Ruggedness
- Fully Characterized Capacitance and Avalanche SOA
- Enhanced body diode dV/dt and dI/dt Capability
- Lead-Free



G	D	S
Gate	Drain	Source

Absolute Maximum Ratings

Symbol	Parameter	Max.	Units
I _D @ T _C = 25°C	Continuous Drain Current, V _{GS} @ 10V (Silicon Limited)	63	A
I _D @ T _C = 100°C	Continuous Drain Current, V _{GS} @ 10V (Silicon Limited)	45	
I _D @ T _C = 25°C	Continuous Drain Current, V _{GS} @ 10V (Package Limited)	56	
I _{DM}	Pulsed Drain Current ①	252	
P _D @ T _C = 25°C	Maximum Power Dissipation	143	W
	Linear Derating Factor	0.95	W/°C
V _{GS}	Gate-to-Source Voltage	± 20	V
T _J	Operating Junction and	-55 to + 175	°C
T _{STG}	Storage Temperature Range		
	Soldering Temperature, for 10 seconds (1.6mm from case)	300	

Avalanche Characteristics

E _{AS} (Thermally limited)	Single Pulse Avalanche Energy ②	127	mJ
I _{AR}	Avalanche Current ①	See Fig. 14, 15, 22a, 22b	A
E _{AR}	Repetitive Avalanche Energy ①		mJ

Thermal Resistance

Symbol	Parameter	Typ.	Max.	Units
R _{θJC}	Junction-to-Case ③	---	1.05	°C/W
R _{θJA}	Junction-to-Ambient (PCB Mount) ⑦	---	50	
R _{θJA}	Junction-to-Ambient	---	110	

ORDERING INFORMATION:

See detailed ordering and shipping information on the last page of this data sheet.

Notes ① through ⑧ are on page 11

www.irf.com

Static @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

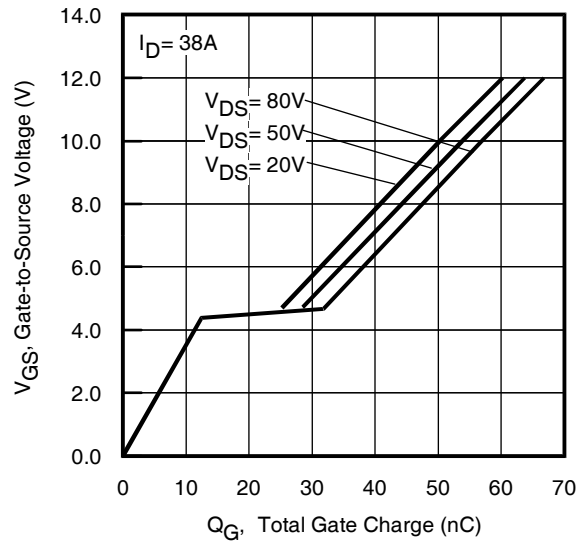
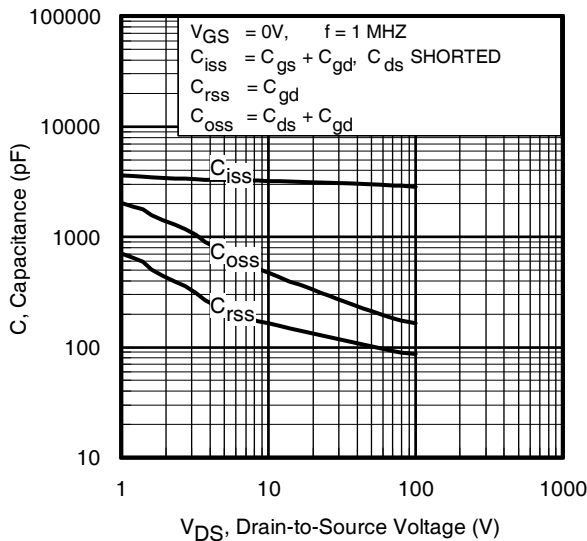
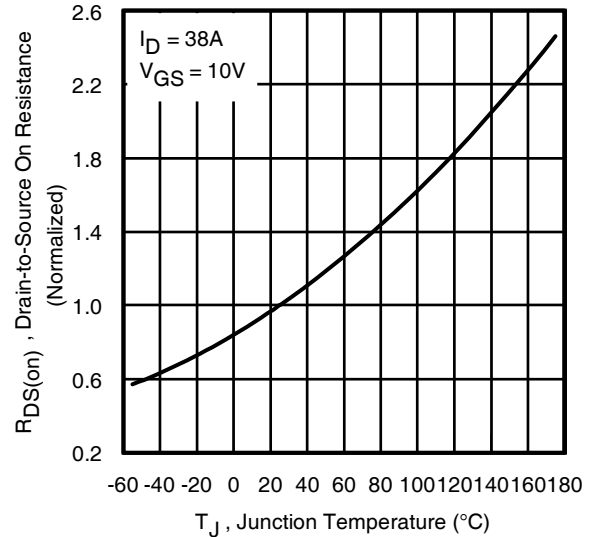
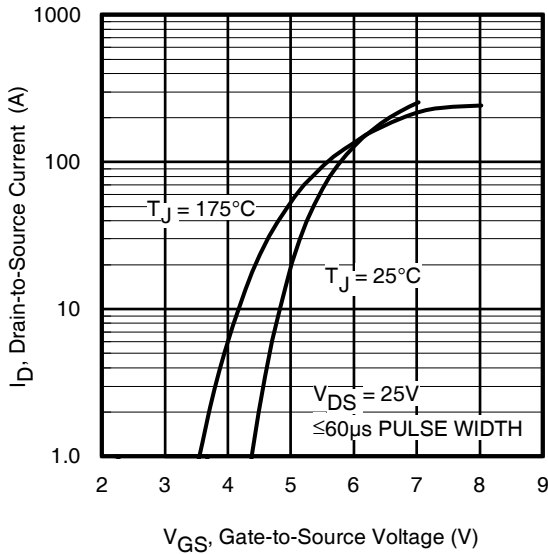
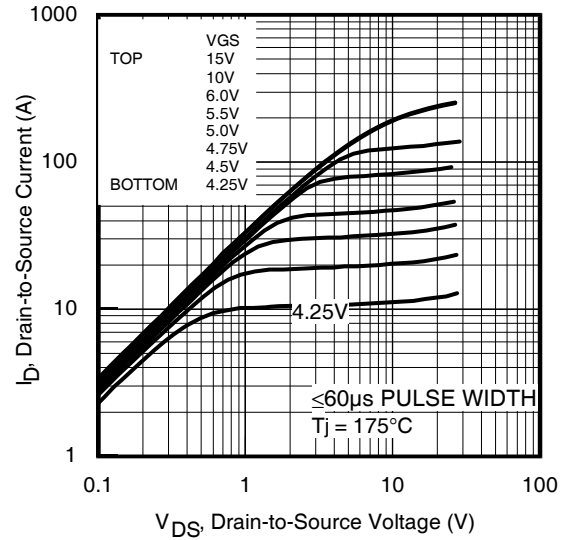
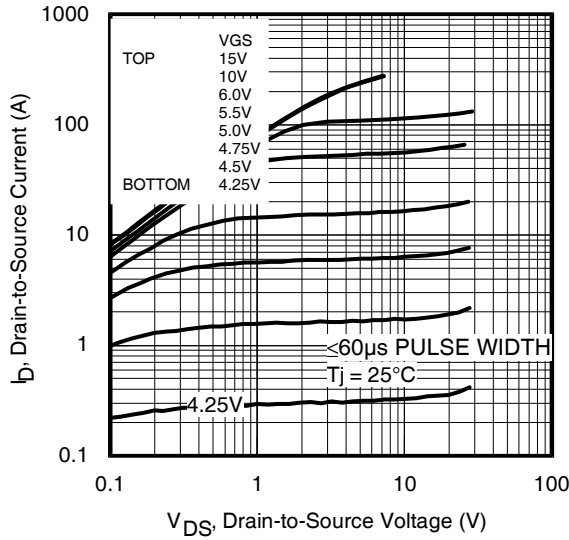
Symbol	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(BR)DSS}$	Drain-to-Source Breakdown Voltage	100	—	—	V	$V_{GS} = 0V, I_D = 250\mu A$
$\Delta V_{(BR)DSS}/\Delta T_J$	Breakdown Voltage Temp. Coefficient	—	0.10	—	V/ $^\circ\text{C}$	Reference to 25°C , $I_D = 5mA$ ①
$R_{DS(on)}$	Static Drain-to-Source On-Resistance	—	11.1	13.9	m Ω	$V_{GS} = 10V, I_D = 38A$ ④
$V_{GS(th)}$	Gate Threshold Voltage	2.0	3.0	4.0	V	$V_{DS} = V_{GS}, I_D = 100\mu A$
I_{DSS}	Drain-to-Source Leakage Current	—	—	20	μA	$V_{DS} = 100V, V_{GS} = 0V$
		—	—	250		$V_{DS} = 100V, V_{GS} = 0V, T_J = 125^\circ\text{C}$
I_{GSS}	Gate-to-Source Forward Leakage	—	—	100	nA	$V_{GS} = 20V$
	Gate-to-Source Reverse Leakage	—	—	-100		$V_{GS} = -20V$
$R_{G(int)}$	Internal Gate Resistance	—	0.61	—	Ω	

Dynamic @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

Symbol	Parameter	Min.	Typ.	Max.	Units	Conditions
g_{fs}	Forward Transconductance	62	—	—	S	$V_{DS} = 25V, I_D = 38A$
Q_g	Total Gate Charge	—	54	81	nC	$I_D = 38A$
Q_{gs}	Gate-to-Source Charge	—	14	—		$V_{DS} = 50V$
Q_{gd}	Gate-to-Drain ("Miller") Charge	—	15	—		$V_{GS} = 10V$ ④
Q_{sync}	Total Gate Charge Sync. ($Q_g - Q_{gd}$)	—	39	—		$I_D = 38A, V_{DS} = 0V, V_{GS} = 10V$
$t_{d(on)}$	Turn-On Delay Time	—	18	—	ns	$V_{DD} = 65V$
t_r	Rise Time	—	42	—		$I_D = 38A$
$t_{d(off)}$	Turn-Off Delay Time	—	42	—		$R_G = 7.5\Omega$
t_f	Fall Time	—	34	—		$V_{GS} = 10V$ ④
C_{iss}	Input Capacitance	—	3031	—	pF	$V_{GS} = 0V$
C_{oss}	Output Capacitance	—	213	—		$V_{DS} = 50V$
C_{rss}	Reverse Transfer Capacitance	—	104	—		$f = 1.0MHz$
$C_{oss \text{ eff. (ER)}}$	Effective Output Capacitance (Energy Related)	—	255	—		$V_{GS} = 0V, V_{DS} = 0V \text{ to } 80V$ ⑥
$C_{oss \text{ eff. (TR)}}$	Effective Output Capacitance (Time Related)	—	478	—		$V_{GS} = 0V, V_{DS} = 0V \text{ to } 80V$ ⑤

Diode Characteristics

Symbol	Parameter	Min.	Typ.	Max.	Units	Conditions
I_S	Continuous Source Current (Body Diode)	—	—	56	A	MOSFET symbol showing the integral reverse p-n junction diode.
I_{SM}	Pulsed Source Current (Body Diode) ①	—	—	252		
V_{SD}	Diode Forward Voltage	—	—	1.3	V	$T_J = 25^\circ\text{C}, I_S = 38A, V_{GS} = 0V$ ④
dv/dt	Peak Diode Recovery	—	7.0	—	V/ns	$T_J = 175^\circ\text{C}, I_S = 38A, V_{DS} = 100V$ ③
t_{rr}	Reverse Recovery Time	—	34	—	ns	$T_J = 25^\circ\text{C}$ $V_R = 86V$
		—	39	—		$T_J = 125^\circ\text{C}$ $I_F = 38A$
Q_{rr}	Reverse Recovery Charge	—	47	—	nC	$T_J = 25^\circ\text{C}$ $di/dt = 100A/\mu s$ ④
		—	61	—		$T_J = 125^\circ\text{C}$
I_{RRM}	Reverse Recovery Current	—	2.4	—	A	$T_J = 25^\circ\text{C}$
t_{on}	Forward Turn-On Time	Intrinsic turn-on time is negligible (turn-on is dominated by LS+LD)				



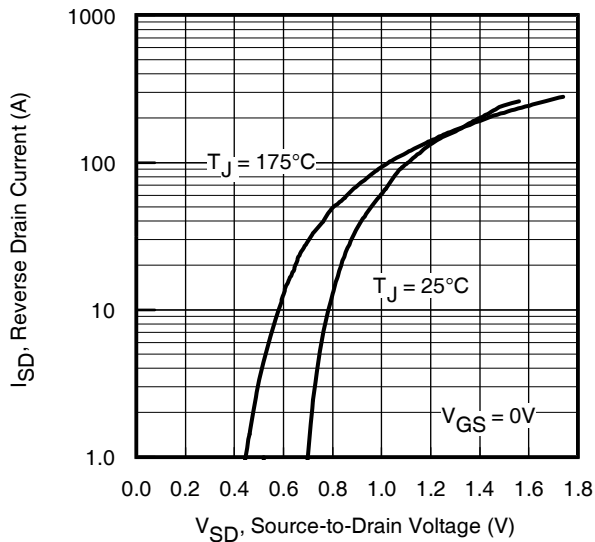


Fig 7. Typical Source-Drain Diode Forward Voltage

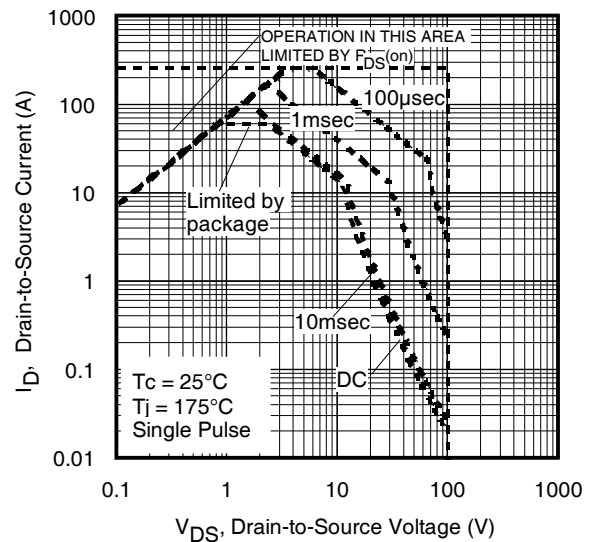


Fig 8. Maximum Safe Operating Area

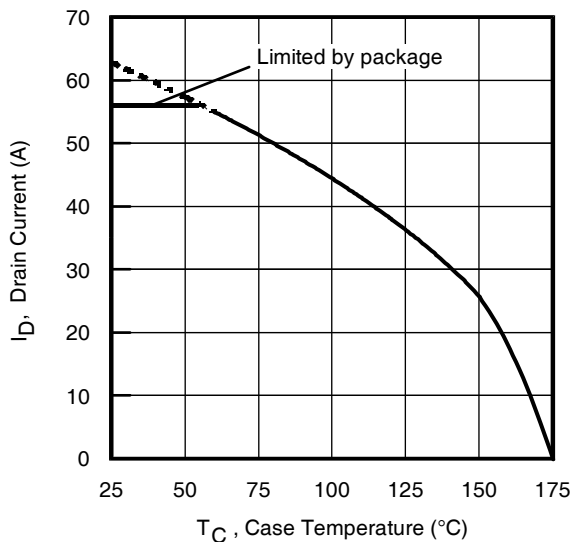


Fig 9. Maximum Drain Current vs. Case Temperature

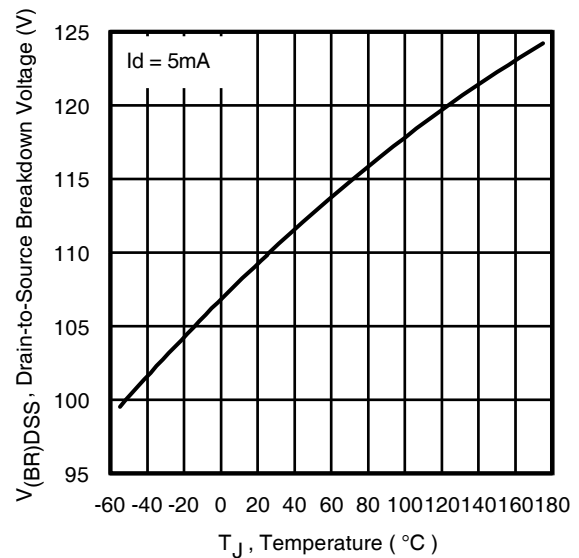


Fig 10. Drain-to-Source Breakdown Voltage

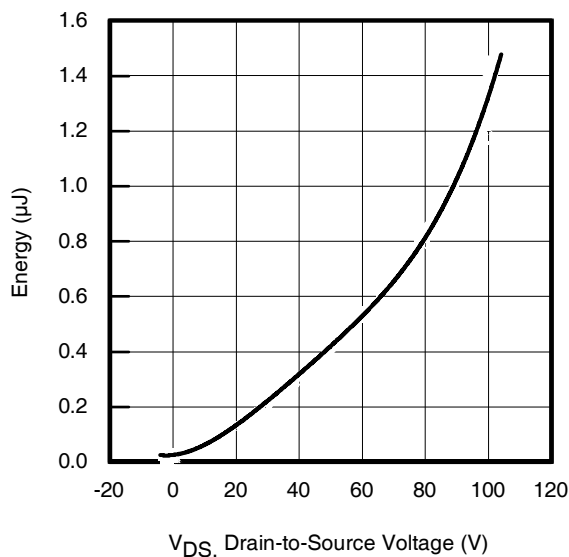


Fig 11. Typical C_{OSS} Stored Energy

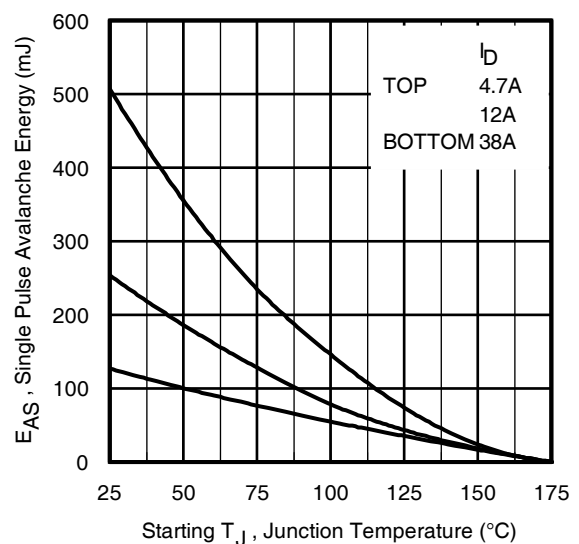


Fig 12. Maximum Avalanche Energy vs. Drain Current

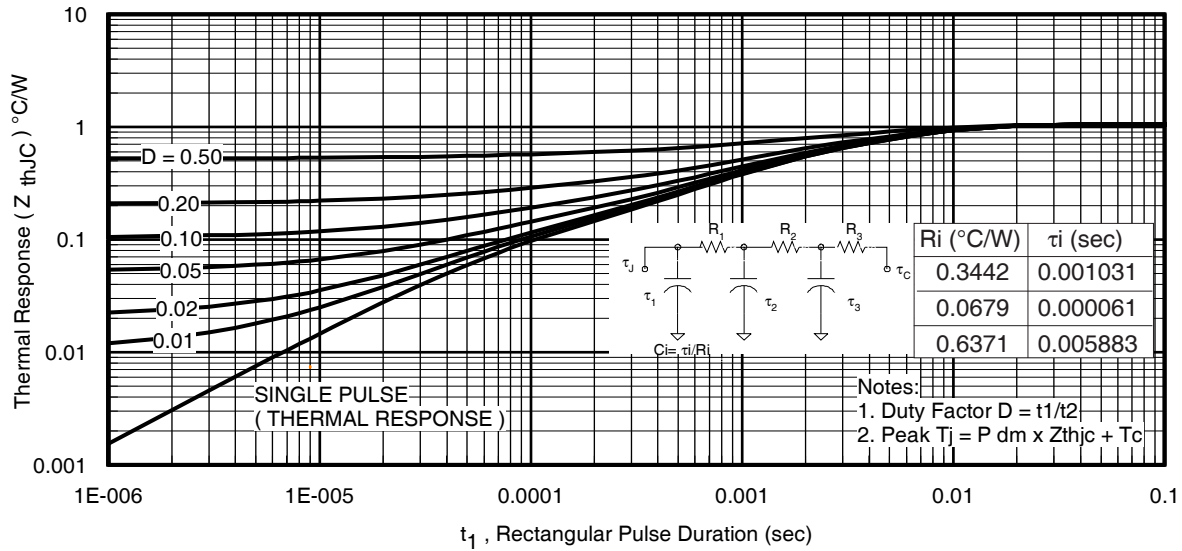


Fig 13. Maximum Effective Transient Thermal Impedance, Junction-to-Case

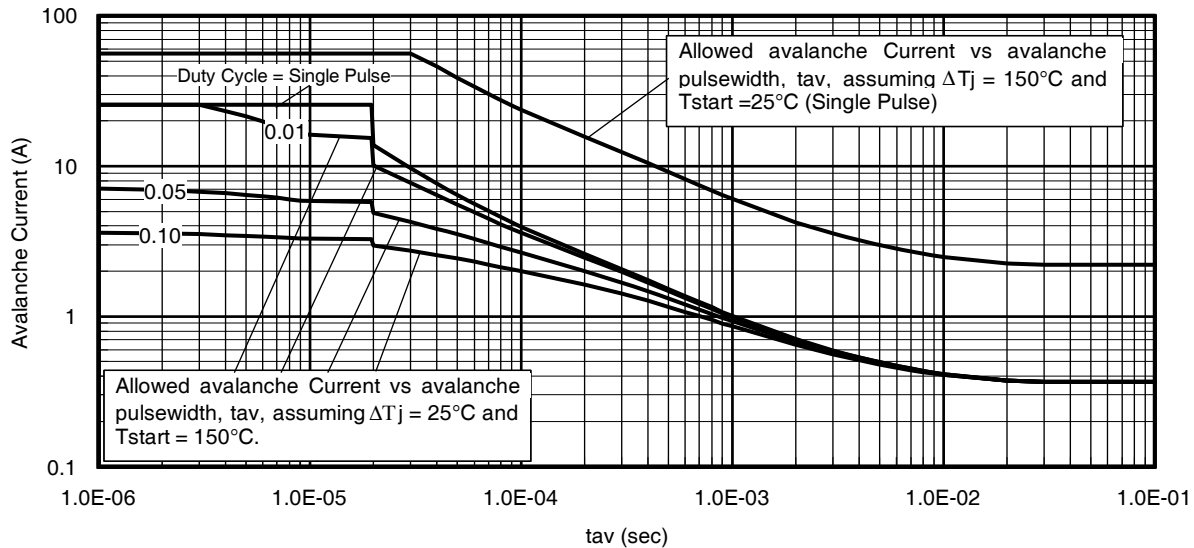


Fig 14. Typical Avalanche Current vs. Pulsewidth

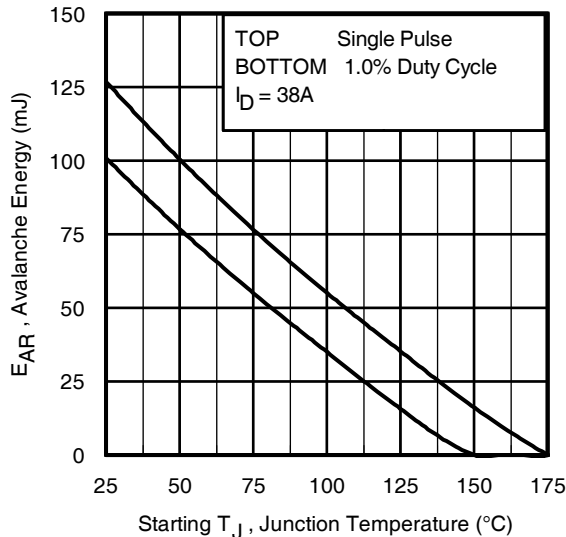


Fig 15. Maximum Avalanche Energy vs. Temperature

Notes on Repetitive Avalanche Curves , Figures 14, 15:
(For further info, see AN-1005 at www.irf.com)

1. Avalanche failures assumption:
Purely a thermal phenomenon and failure occurs at a temperature far in excess of T_{jmax} . This is validated for every part type.
2. Safe operation in Avalanche is allowed as long as T_{jmax} is not exceeded.
3. Equation below based on circuit and waveforms shown in Figures 16a, 16b.
4. $P_{D(ave)}$ = Average power dissipation per single avalanche pulse.
5. BV = Rated breakdown voltage (1.3 factor accounts for voltage increase during avalanche).
6. I_{av} = Allowable avalanche current.
7. ΔT = Allowable rise in junction temperature, not to exceed T_{jmax} (assumed as 25°C in Figure 14, 15).
 t_{av} = Average time in avalanche.
 D = Duty cycle in avalanche = $t_{av} \cdot f$
 $Z_{thJC}(D, t_{av})$ = Transient thermal resistance, see Figures 13)

$$P_{D(ave)} = 1/2 (1.3 \cdot BV \cdot I_{av}) = \Delta T / Z_{thJC}$$

$$I_{av} = 2\Delta T / [1.3 \cdot BV \cdot Z_{th}]$$

$$E_{AS(AR)} = P_{D(ave)} \cdot t_{av}$$

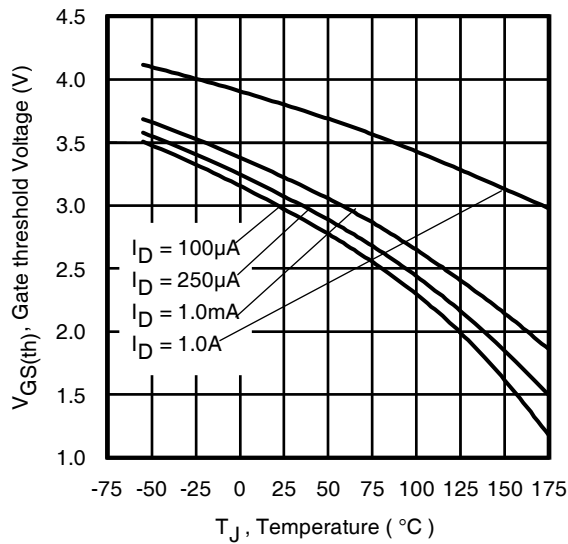


Fig. 16. Threshold Voltage vs. Temperature

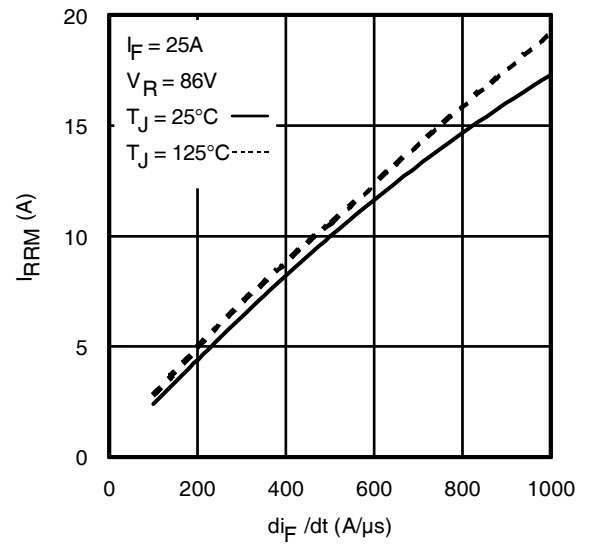


Fig. 17 - Typical Recovery Current vs. di_F/dt

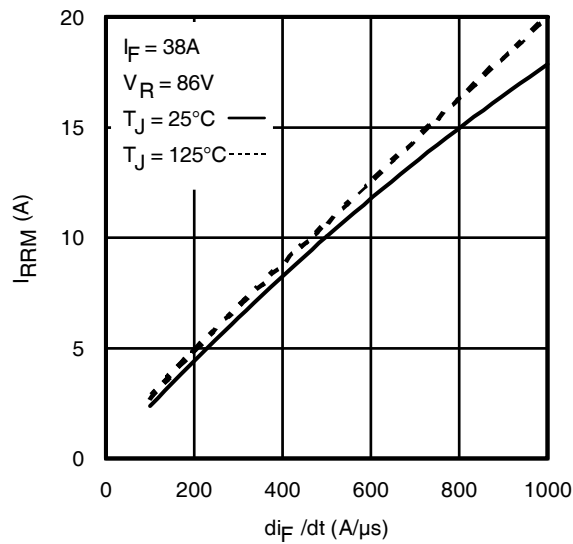


Fig. 18 - Typical Recovery Current vs. di_F/dt

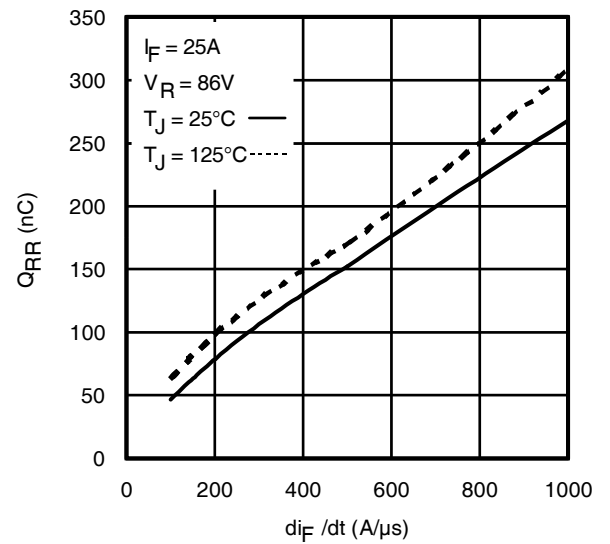


Fig. 19 - Typical Stored Charge vs. di_F/dt

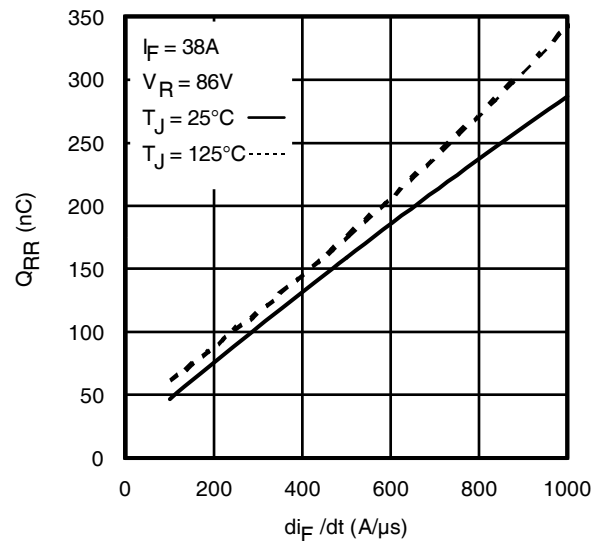


Fig. 20 - Typical Stored Charge vs. di_F/dt

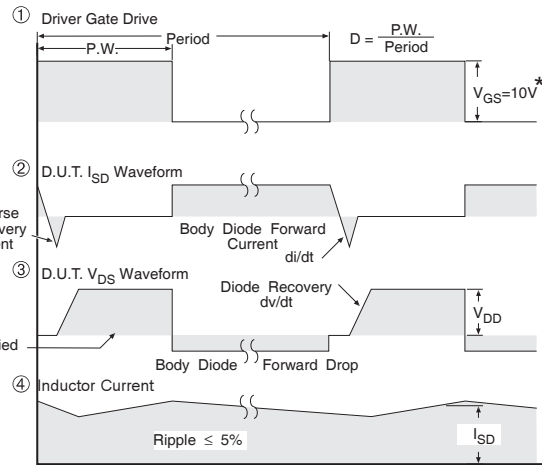
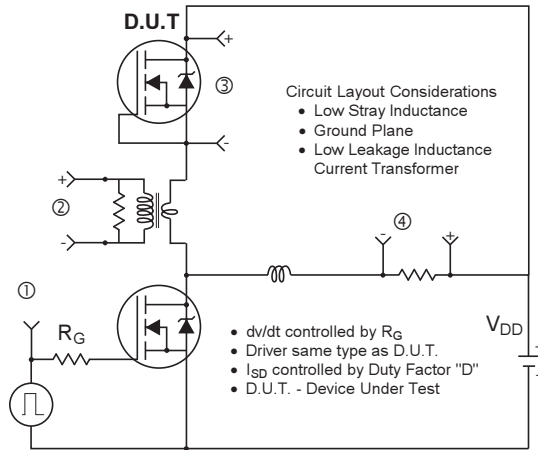


Fig 21. Peak Diode Recovery dv/dt Test Circuit for N-Channel HEXFET® Power MOSFETs

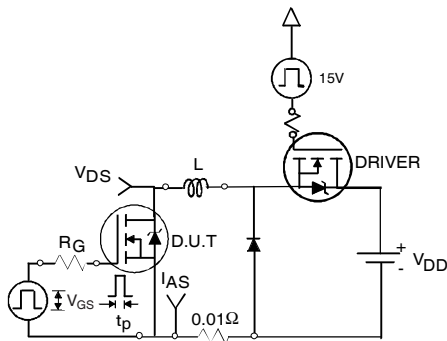


Fig 22a. Unclamped Inductive Test Circuit

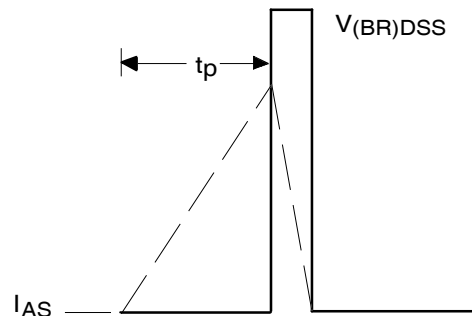


Fig 22b. Unclamped Inductive Waveforms

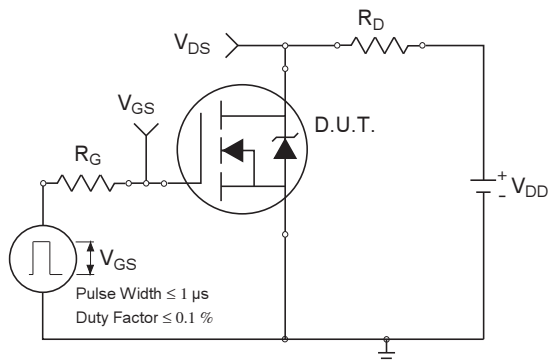


Fig 23a. Switching Time Test Circuit

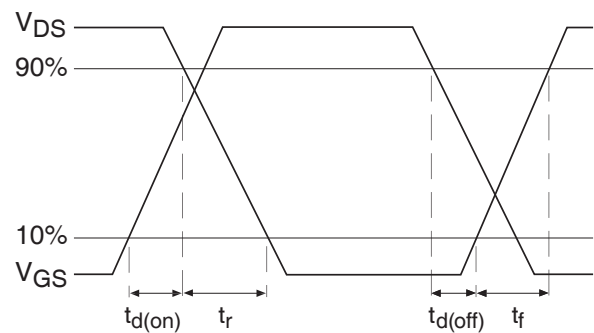


Fig 23b. Switching Time Waveforms

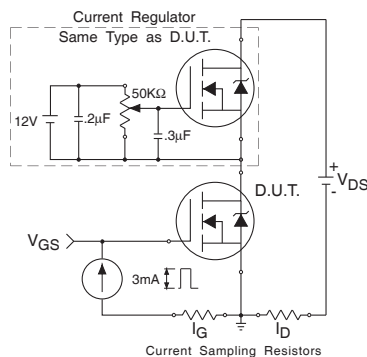


Fig 24a. Gate Charge Test Circuit

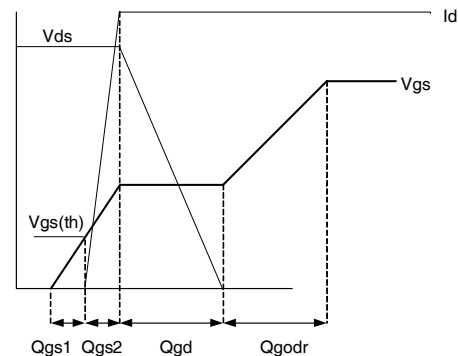
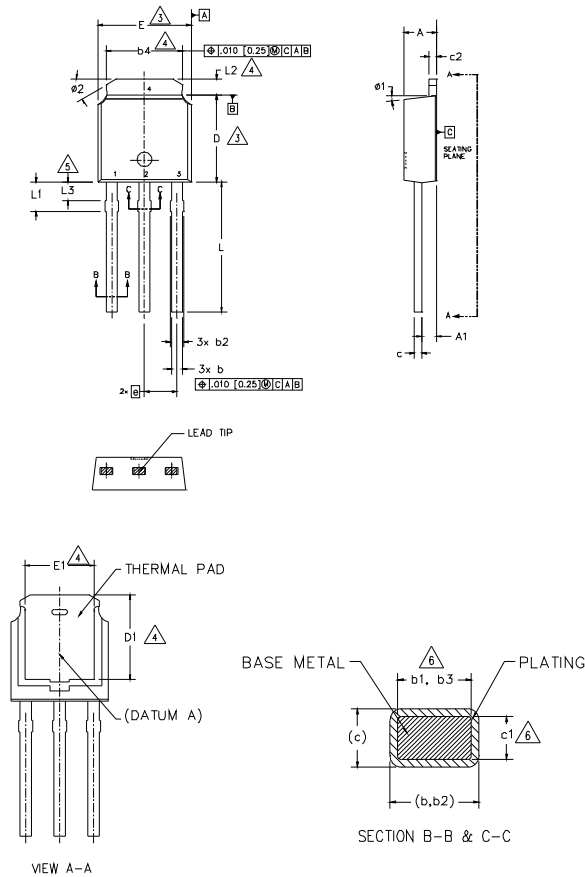


Fig 24b. Gate Charge Waveform

I-Pak (TO-251AA) Package Outline

Dimensions are shown in millimeters (inches)



NOTES:

- 1.- DIMENSIONING AND TOLERANCING PER ASME Y14.5M-1994
- 2.- DIMENSIONS ARE SHOWN IN INCHES [MILLIMETERS].
- 3.- DIMENSION D & E DO NOT INCLUDE MOLD FLASH. MOLD FLASH SHALL NOT EXCEED .005 [0.13] PER SIDE. THESE DIMENSIONS ARE MEASURED AT THE OUTMOST EXTREMES OF THE PLASTIC BODY.
- 4.- THERMAL PAD CONTOUR OPTION WITHIN DIMENSION b4, L2, E1 & D1.
- 5.- LEAD DIMENSION UNCONTROLLED IN L3.
- 6.- DIMENSION b1, b3 & c1 APPLY TO BASE METAL ONLY.
- 7.- OUTLINE CONFORMS TO JEDEC OUTLINE TO-251AA (Date 06/02).
- 8.- CONTROLLING DIMENSION : INCHES.

SYMBOL	DIMENSIONS				NOTES
	MILLIMETERS		INCHES		
	MIN.	MAX.	MIN.	MAX.	
A	2.18	2.39	.086	.094	
A1	0.89	1.14	.035	.045	
b	0.64	0.89	.025	.035	
b1	0.65	0.79	.025	.031	6
b2	0.76	1.14	.030	.045	
b3	0.76	1.04	.030	.041	6
b4	4.95	5.46	.195	.215	4
c	0.46	0.61	.018	.024	
c1	0.41	0.56	.016	.022	6
c2	0.46	0.89	.018	.035	
D	5.97	6.22	.235	.245	3
D1	5.21	—	.205	—	4
E	6.35	6.73	.250	.265	3
E1	4.32	—	.170	—	4
e	2.29 BSC		.090 BSC		
L	8.89	9.65	.350	.380	
L1	1.91	2.29	.045	.090	
L2	0.89	1.27	.035	.050	4
L3	1.14	1.52	.045	.060	5
ø1	0°	15°	0°	15°	
ø2	25°	35°	25°	35°	

LEAD ASSIGNMENTS

HEXFET

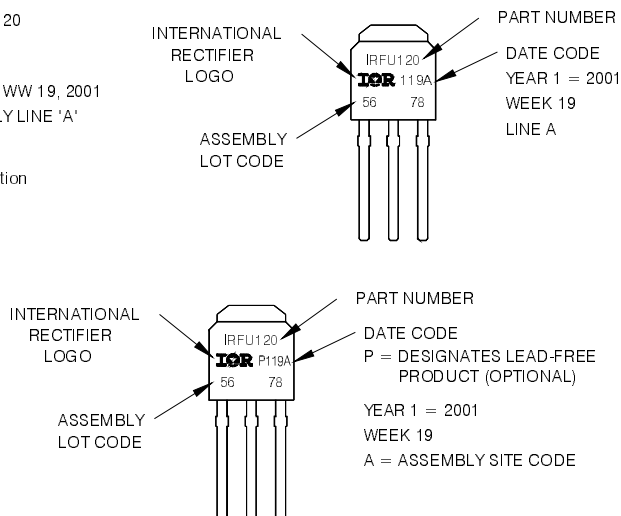
- 1.- GATE
- 2.- DRAIN
- 3.- SOURCE
- 4.- DRAIN

I-Pak (TO-251AA) Part Marking Information

EXAMPLE: THIS IS AN IRFU120
WITH ASSEMBLY
LOT CODE 5678
ASSEMBLED ON WW 19, 2001
IN THE ASSEMBLY LINE 'A'

Note: 'P' in assembly line position
indicates Lead-Free

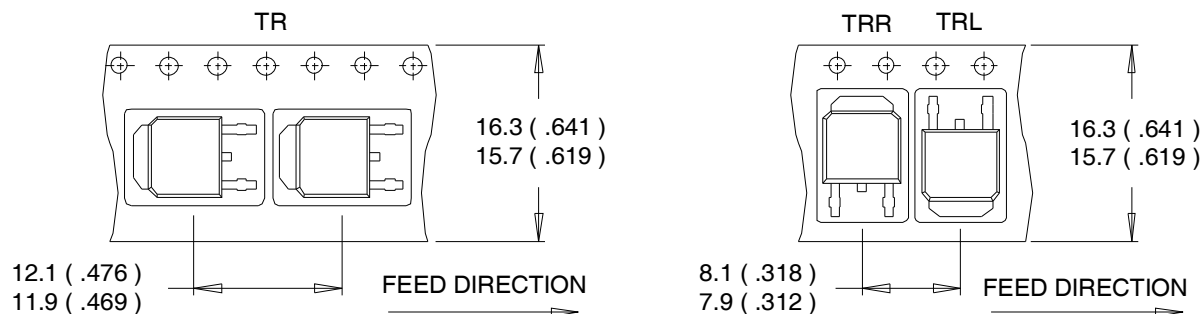
OR



Note: For the most current drawing please refer to IR website at <http://www.irf.com/package/>
www.irf.com

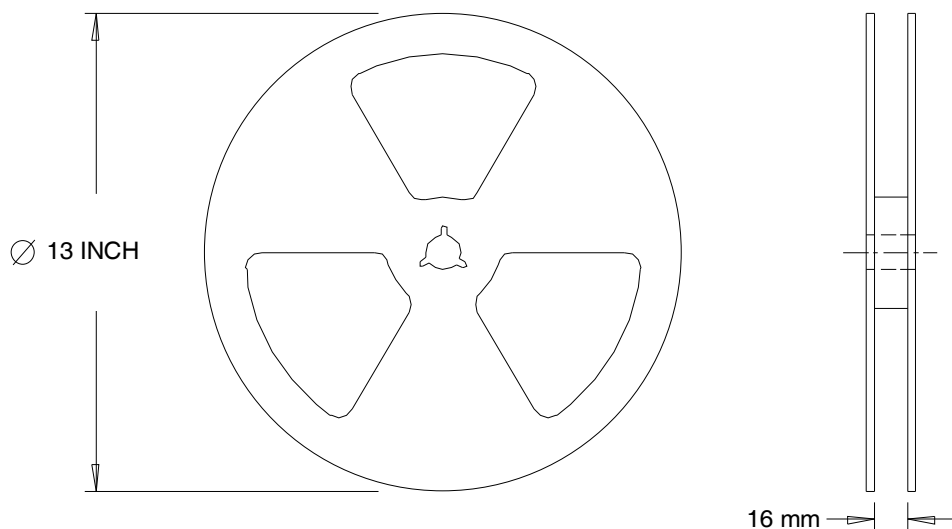
D-Pak (TO-252AA) Tape & Reel Information

Dimensions are shown in millimeters (inches)



NOTES :

1. CONTROLLING DIMENSION : MILLIMETER.
2. ALL DIMENSIONS ARE SHOWN IN MILLIMETERS (INCHES).
3. OUTLINE CONFORMS TO EIA-481 & EIA-541.



NOTES :

1. OUTLINE CONFORMS TO EIA-481.

Orderable part number	Package Type	Standard Pack		Note
		Form	Quantity	
IRFR4510PbF	D-PAK	Tube/Bulk	75	
IRFR4510TRPbF	D-PAK	Tape and Reel	2000	
IRFU4510PbF	I-PAK	Tube/Bulk	75	

Qualification Information[†]

Qualification level	Industrial ^{††}	
	(per JEDEC JESD47F ^{†††} guidelines)	
	Comments: This family of products has passed JEDEC's Industrial qualification. IR's Consumer qualification level is granted by extension of the higher Industrial level.	
Moisture Sensitivity Level	D-PAK	MSL1 (per JEDEC J-STD-020D ^{†††})
	I-PAK	Not applicable
RoHS Compliant	Yes	

† Qualification standards can be found at International Rectifier's web site <http://www.irf.com/product-info/reliability>

†† Higher qualification ratings may be available should the user have such requirements. Please contact your International Rectifier sales representative for further information: <http://www.irf.com/whoto-call/salesrep/>

††† Applicable version of JEDEC standard at the time of product release.

Notes:

- ① Repetitive rating; pulse width limited by max. junction temperature.
- ② Limited by T_{Jmax} , starting $T_J = 25^{\circ}C$, $L = 0.18mH$
 $R_G = 50\Omega$, $I_{AS} = 38A$, $V_{GS} = 10V$. Part not recommended for use above this value.
- ③ $I_{SD} \leq 38A$, $di/dt \leq 2031A/\mu s$, $V_{DD} \leq V_{(BR)DSS}$, $T_J \leq 175^{\circ}C$.
- ④ Pulse width $\leq 400\mu s$; duty cycle $\leq 2\%$.

- ⑤ C_{OSS} eff. (TR) is a fixed capacitance that gives the same charging time as C_{OSS} while V_{DS} is rising from 0 to 80% V_{DSS} .
- ⑥ C_{OSS} eff. (ER) is a fixed capacitance that gives the same energy as C_{OSS} while V_{DS} is rising from 0 to 80% V_{DSS} .
- ⑦ When mounted on 1" square PCB (FR-4 or G-10 Material). For recommended footprint and soldering techniques refer to application note #AN-994.
- ⑧ R_{θ} is measured at T_J approximately $90^{\circ}C$.

Data and specifications subject to change without notice

International
IR Rectifier

IR WORLD HEADQUARTERS: 101 N. Sepulveda Blvd., El Segundo, California 90245, USA Tel: (310) 252-7105
TAC Fax: (310) 252-7903

Visit us at www.irf.com for sales contact information. 05/2012